P-Channel Enhancement Mode Field Effect Transistor

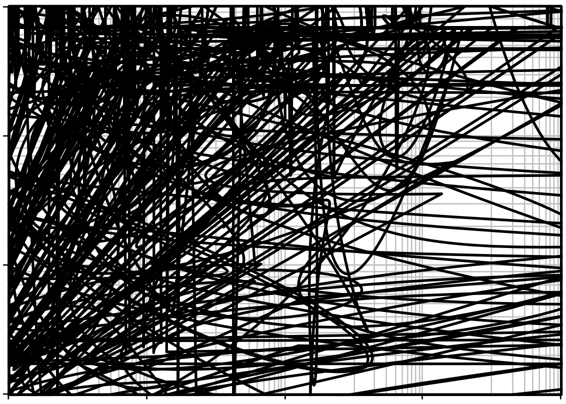
Product Summary

V_{DS}	-60 V
I_D	-100 A
$R_{DS(ON)}$(at V_{GS}=-10V)	8.8mΩ
$R_{DS(ON)}$(at V_{GS}=-6V)	10mΩ
100% EAS Tested1	

■ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	[redacted]

YJB100GP06H



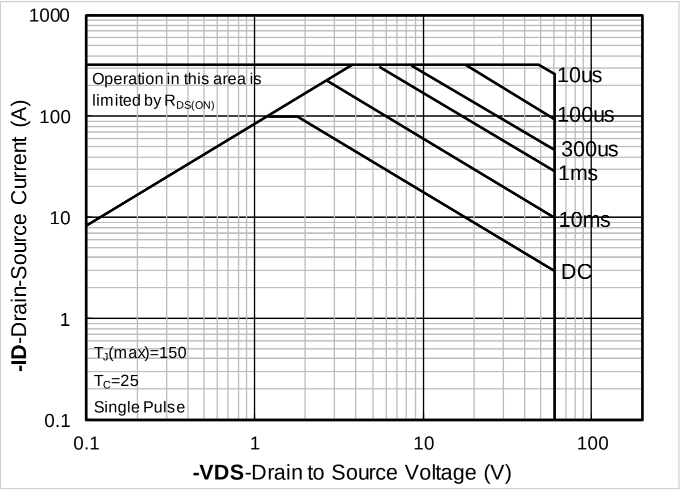


Figure 13. Maximum Transient Thermal Impedance

Figure

■TO-263-HY Package information

SYM_	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes wu Ya n ce ThsElncEBTf3(ti28(c))6(a)-3(ti)7(o)-39 n o th n poecTs2-108(d)-5(i)-47121(p)lgye7(o)d39 n Elnrehn